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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

Confirmation No.: UNASSIGNED

ITO et al.

Group Art Unit: 1765

Appln. No.: 09/361,980

Examiner: L. Umez-Eronini

Filed: July 28, 1999

Title: METHOD OF ETCHING METALLIC THIN
FILM ON THIN FILM RESISTOR

RECEIVED
JUN 14 2001
TC 1700 MAIL ROOM

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01 FC:102
02 FC:103

160.00 OP
126.00 OP

June 12, 2001

AMENDMENT

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

In reply to the Office Action dated February 14, 2001, the period for response to which was extended to June 20 in the March 20 Office Action, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 4, delete the entire paragraph starting at line 4 and replace it with the following new text.

-- According to a third aspect of the present invention, a conductive film is formed on a metallic film to have a thickness equal to or less than 300 nm, and the conductive film is patterned to have an upper surface area, a ratio of which relative to an upper surface area of a thin film resistor is equal to or more than 0.02. Then, the metallic film is etched through an opening of the conductive film. Accordingly, a variation in an etching amount produced due

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